

We claim:

1. A composition, comprising;
 - A) a water soluble organic solvent,
 - 5 B) a sulfonic acid or its corresponding salt, and
 - C) water.
2. The composition as claimed in claim 1, further comprising a corrosion inhibitor.
3. The composition as claimed in claim 1, wherein the water soluble organic
10 solvent is monoethanolamine, N-methylethanolamine, dimethylsulfoxide, dimethylacetamide or mixtures thereof.
4. The composition as claimed in claim 1, wherein the sulfonic acid or its corresponding salt is p-toluene sulfonic acid, 1,5-naphthalene disulfonic acid, 4-ethylbenzene sulfonic acid, dodecylbenzene sulfonic acid or mixtures thereof.
- 15 5. The composition as claimed in claim 2, wherein the corrosion inhibitor is gallic acid, catechol, benzotriazole, benzoic acid, malonic acid, ammonium malonate or mixtures thereof.
6. A composition, comprising;
 - A) from 30 to 85 wt % of a water soluble organic solvent,
 - 20 B) from 1 to 20 wt % of a sulfonic acid or its corresponding salt,
 - C) from 5 to 50 wt % water.
7. The composition as claimed in claim 6, further comprising; from 0.1 to 15 wt % of a corrosion inhibitor.
8. A method of removing photoresist, etch and/or ash residue, or
25 contaminants from a semiconductor substrate, comprising; contacting the semiconductor substrate with a composition, comprising:
 - A) a water soluble organic solvent,
 - B) a sulfonic acid or its corresponding salt, and
 - C) water;
- 30 for a period of time sufficient to remove the photoresist, etch and/or ash residue, or contaminants.

9. The method as claimed in claim 8, wherein the composition further comprises a corrosion inhibitor.

10. The method as claimed in claim 8, wherein the water soluble organic solvent is monoethanolamine, N-methylethanolamine, dimethylsulfoxide,

5 dimethylacetamide or mixtures thereof.

11. The method as claimed in claim 8, wherein the sulfonic acid or its corresponding salt is p-toluene sulfonic acid, 1,5-naphthalene disulfonic acid, 4-ethylbenzene sulfonic acid, dodecylbenzene sulfonic acid or mixtures thereof.

12. The method as claimed in claim 9, wherein the corrosion inhibitor is gallic
10 acid, catechol, benzotriazole, benzoic acid, malonic acid, ammonium malonate or mixtures thereof.